Amendments to the Specification:

Please replace the paragraph numbered 0021 with the following rewritten paragraph:

[0021] The distance from the slit to the substrate can be adjusted within the limits set by the geometry of the deposition system, but that with suitable optimization of the slit size, flow rate, temperature (and hence pressure in the box) good uniformity across a very long exit slit can be obtained even at close slit to substrate distances (i.e. 1 cm or less). This leads to the embodiment shown in FIG. 2, where multiple exit nozzles are used to achieve coarse patterning of the organic semiconductor in a technique analogous to (but distinct from) inkjet printing. Micron-scale nozzles fabricated using microfluidic techniques could yield micron-scale patterned film deposition on the substrate. In yet another embodiment, each nozzle could be connected to a distinct source reservoir and be controlled at a separate temperature permitting, for example, the simultaneous deposition of red, blue and green light emitting layers on a moving web or, for transistor applications, p-type materials, n-type materials and metallic organic materials for heterogeneous integration of organic electronic circuitry. Lateral jitter in the substrate position could be used to sharpen the Gaussian lineshape expected at the edge of each pattern and a small shutter installed over each nozzle could provide for patterning in the direction of substrate transport.